

Freeform Search

Database:

US Pre-Grant Publication Full-Text Database
 US Patents Full-Text Database
 US OCR Full-Text Database
 EPO Abstracts Database
 JPO Abstracts Database
 Derwent World Patents Index
 IBM Technical Disclosure Bulletins

Term:

5449637.pn.

Display: Documents in Display Format: Starting with Number Generate: ☐ Hit List ☒ Hit Count ☐ Side by Side ☐ Image

Search

Clear

Interrupt

Search History

DATE: Wednesday, January 05, 2005 [Printable Copy](#) [Create Case](#)

Set Name Query

side by side

Hit Count Set Name

result set

DB=USPT; PLUR=YES; OP=OR

L7 5449637.pn.1 L7L6 6268633.pn.1 L6

DB=PGPB,USPT,USOC,EPAB,JPAB,DWPI,TDBD; PLUR=YES; OP=OR

L5 6268633.pn.2 L5L4 L3 not L2263 L4L3 L1 and (deposit\$3 with (oxide or insulat\$4) with drain) and (mask with drain)268 L3L2 L1 and (screen with (source or drain))215 L2L1 (transistor or MOSFET) with (HV or (high adj voltage) or (high adj breakdown))33568 L1

END OF SEARCH HISTORY

Freeform Search

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Term:

(low adj voltage adj transistor) and (high adj
 voltage adj transistor) and (drain adj extension)

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<u>Set</u> <u>Name</u> side by side	<u>Query</u>	<u>Hit</u> <u>Count</u>	<u>Set</u> <u>Nam</u> result s
<u>L1</u>	DB=PGPB,USPT,USOC,EPAB,JPAB,DWPI,TDBD; PLUR=YES; OP=OR (low adj voltage adj transistor) and (high adj voltage adj transistor) and (drain adj extension)	86	<u>L1</u>

END OF SEARCH HISTORY